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TS105-1 红外温度传感器



Thermopiles are used for non-contact surface temperature measuring. Any object emits infrared radiation. The radiation power is increasing with growing surface temperatures. Based on this relation, Thermopile measure the emitted power and determine the object's temperature precisely.

Thermopiles are based on the Seebeck effect, which is used since a long time for conventional thermocouples. The application of micromechanics and thin film technology allows the production of miniaturized and cost effective sensor elements. A multitude of thermojunctions deposited on a silicon substrate is connected in series to form a Thermopile. The hot junctions are thermally insulated from the cold junctions on the substrate by etching a self-supporting extremely thin membrane. An absorbing layer on the hot junctions transforms the incoming radiation into heat. A voltage proportional to the radiation is generated by the thermoelectric effect. The sensors are delivered in TO18-packages. Different housings and filter types can be selected to find an optimal solution for each application. Chips without housing are available as well.

Parameter	Symbol	Llnit	Value	Condition
	Symbol	Unit	Value	Condition
Number of thermojunctions	n		100	
Material			BiSb, NiCr	
Active Area	A _A	mm²	0.7 × 0.7	
Chip Size	A _C	mm²	2.0 × 2.0	
Resistance of Thermopiles	R	kΩ	50 ± 15	25 °C
TC of resistance	TCR	% / K	$\textbf{-0.03} \pm \textbf{0.02}$	+25~+75 ℃
Sensitivity of sensor	Sc	V/W	typical 100	25 ℃, 500 K, D
TC of sensitivity	TČS	% / K	-0.52 ± 0.08	+25~+75 ℃
Specific detectivity	D*	cm*Hz ^{1/2} / W	2.1 × 10 ⁸	500 K, DC
Noise equivalent power	NEP	nW	0.38	500 K, 1 Hz
Noise voltage	U _N	nV / Hz ^{1/2}	37	500 K, 1 Hz
Time constant (preliminary)	t ₆₃	ms	40± 10	500 K, 1 Hz
Operation temperature	Т	°C	-20 100	
Storage temperature	Т	°C	-40 100	
Field of View	FOV	0	110	
Reference Resistor(Ni-PTC)	R _{NTC}	Ω	$1000\pm0.4\%$	0 °C
TC of resistance	TCR	ppm / K	6178 ± 1%	0 ~ 100 ℃



TS105-2

TS105-3

工作原理

术语解释

应用手册

其他TS产品

<u>TS118-2</u>

<u>TS118-3</u>

<u>TS118-5</u>





absorption area (hot junctions) SiNx-membrane silicon substrate (cold junctions)





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50

60

70

80

90

100

1291,1

1353,4

1417,2

1482,5

1549,3

1617,8

1297,2

1359,7

1423,7

1489.1

1556.1

1624,7

1303,4

1366,0

1430,1

1495,7

1562.9

1631,7

1309,6

1372,4

1436,6

1502,4

1569.7

1638,6

1315,8

1378,7

1443,1

1509,1

1576,5

1645,6

1322,0

1385,1

1449,7

1515,7

1583,4

1652,6

1328,3

1391,5

1456,2

1522,4

1590,2

1659,6

1334,5

1397,9

1462,8

1529,1

1597,1

1666,7

1340,8

1404,3

1469,3

1535,9

1604.0

1673,7

1347,1

1410,8 1475,9

1542,6

1610,9

1680,8

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TS105-1 output voltage vs temperature(calculated)

T _{anb} / °C	UTP_obj / µV														
	0	10	20	30	40	50	60	70	80	90	100	110	120	130	140
10	-385	0	428	926	1491	2157	2902	3597	4406	5308	6408	7375	8549	9788	11177
20	-779	-410	1	478	1021	1660	2375	3042	3818	4684	5739	6667	7794	8983	10317
30	-1205	-851	-458	0	520	1132	1817	2456	3200	4030	5040	5929	7009	8148	9425
40	-1649	-1311	-935	-497	0	585	1240	1851	2562	3356	4322	5172	6204	7293	8515
50	-2132	-1810	-1451	-1033	-559	0	625	1207	1886	2643	3565	4376	5361	6400	7566
50 - 2132 - 1810 - 1451 - 1033 - 559 0 625 1207 1886 2643 3565 4376 5361 6400 7566															



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